

QP2-6 TO5

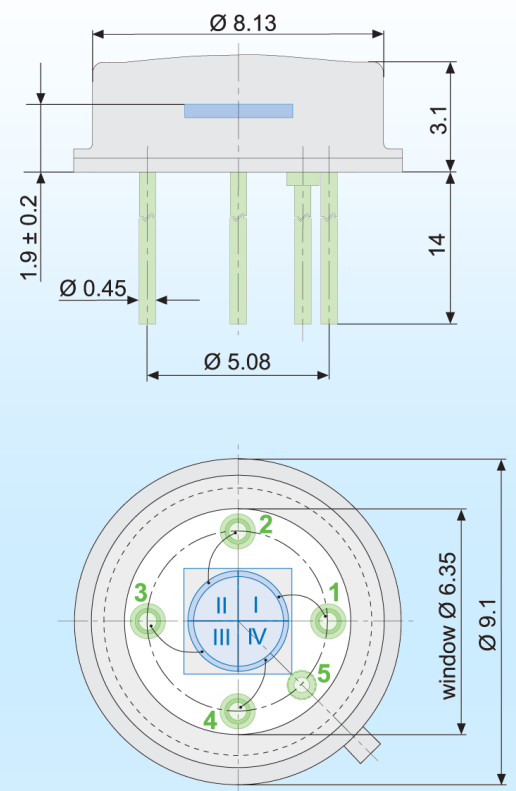
Quadrant Photodiode

Special characteristics:

Small gap
Low dark current
High shunt resistance
High resolution

Parameters:	QP2-6 TO5
Elements*	4
Active Area	2mm ² Ø 1,6mm
Gap (µm)	20, Oxid
Dimensional outline	
window material	clear glass
operating temperatur	-40 ..+100 °C
storage temperatur	-55 ..+125 °C
Spectral Responsivity (A/W)	
(633 nm)	typ. 0,4
(900 nm)	typ. 0,64
Dark current (nA)	
(10 V)	typ. 0,1*
Breakdown voltage (V)	
at I _D = 2 µA (V)	15
Capacitance (pF)	
10 V	max.2*
Rise time (ns)	
850 nm, 10 V, 50 Ω	20
Uniformity of Sensivity	
	typ. ± 1 % max. ± 2 %

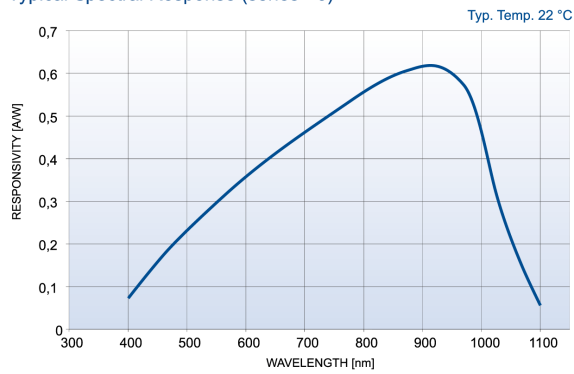
Package (TO5):



Pin-Connection

Pin-No.	Connection
1	Anode 1
2	Anode 2
3	Anode 3
4	Anode 4
5	Cathode/ Case

Typical Spectral Response (series - 6)



Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

Handling Precautions:

soldering temperature: 260 °C for max. 10 s. The device must be protected against solder flux vapour!
min. Pin - length: 2 mm
ESD - protection: Standard precautionary measures are sufficient.
Storage: Store devices in conductive foam.
Avoid skin contact with window!
Clean window with Ethyl alcohol if necessary.
Do not scratch or abrade window.

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